

EUROPEAN PATENT OFFICE
U.S. PATENT AND TRADEMARK OFFICE

CPC NOTICE OF CHANGES 30

DATE: SEPTEMBER 1, 2014

PROJECT RP0032

The following classification changes will be effected by this Notice of Changes:

Action*	Subclass	Group(s)
Symbols deleted:	H01L	29/784
	H01L	29/804
New symbols:	H01L	29/78391
	H01L	29/803
Title Change:	H01L	29/778
	H01L	29/788

This Notice of Changes includes the following *[Check the ones included]:*

1. CLASSIFICATION SCHEME CHANGES
 - A. New, Deleted, and Modified group(s)
 - B. New, Deleted, and Modified Warning Notice(s)
 - C. New, Deleted, and Modified Note(s)
2. DEFINITIONS
3. REVISION CONCORDANCE LIST (RCL)
4. CHANGES TO THE CPC-TO-IPC CONCORDANCE LIST (CICL)
5. CROSS-REFERENCE LIST (CRL)

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1. CLASSIFICATION SCHEME CHANGES

A. New, Deleted, and Modified group(s)

SUBCLASS H01L - SEMICONDUCTOR DEVICES; ELECTRIC SOLID STATE DEVICES NOT OTHERWISE PROVIDED FOR

<u>Type*</u>	<u>Symbol</u>	<u>Intent Level</u>	<u>Title</u>
M	29/778	4	with two-dimensional charge carrier gas channel, e.g. HEMT; { with two-dimensional charge-carrier layer formed at a heterojunction interface (H01L29/803 takes precedence) }
U	29/7839	6	{ with Schottky drain or source contact }
N	29/78391	6	{the gate comprising a layer which is used for its ferroelectric properties}
D	29/784	6	< administrative transfer to H01L29/78391 >
M	29/788	6	with floating gate { (H01L29/78391 takes precedence) }
U	29/802	6	{ with heterojunction gate, e.g. transistors with semiconductor layer acting as gate insulating layer, MIS-like transistors (H01L 29/806 takes precedence; with one dimensional electron gas H01L 29/775 ; with dimensional electron gas H01L 29/778) }
N	29/803	7	{Programmable transistors, e.g. with charge-trapping quantum well}
D	29/804	7	< administrative transfer to H01L29/803 >

*N = new entries, C = entries with modified file scope, M = subclasses or groups do not impact the file scope, D = deleted entries, U = entries that are unchanged, but presented in order to show the hierarchy of the scheme to simplify understanding

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2. Deleted and Modified Definitions

SUBCLASS H01L - SEMICONDUCTOR DEVICES; ELECTRIC SOLID STATE DEVICES NOT OTHERWISE PROVIDED FOR

<u>Type*</u>	<u>In the Definition of</u>	<u>Specific Location</u>	<u>Old</u>	<u>Action</u>
M	H01L27/11585	Informative reference	H01L29/784	Change to H01L29/78391

*M = modified definition; D = deleted definition

[H01L27/11585](#)

[N: with gate electrode comprising a layer which is used for its ferroelectric memory properties, e.g. MFS (metalferroelectric- \semiconductor), MFMIS (metal-ferroelectricmetal-insulator-semiconductor)]

Informative references

Attention is drawn to the following places, which may be of interest for search:

Memory transistors with a ferroelectric layer in the gate stack per se	H01L29/78391
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3. REVISION CONCORDANCE LIST (RCL)

From CPC Symbol	To CPC Symbol
H01L 29/784	H01L29/78391
H01L 29/804	H01L29/803

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4. CHANGES TO THE CPC-TO-IPC CONCORDANCE LIST (**CICL**)

CPC	IPC	Action
H01L 29/784		Delete entire entry
H01L 29/804		Delete entire entry
H01L 29/78391	H01L 29/78	Add
H01L 29/803	H01L 29/80	Add

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5. CHANGES TO THE CROSS REFERENNCE LIST (CRL)

Scheme references impacted by this revision project

<u>Location of reference to be changed</u>	<u>Referenced subclass or group to be changed</u>	<u>Changed to</u>
H01L 29/778	H01L 29/804	H01L 29/803
H01L 29/788	H01L 29/784	H01L 29/78391

Definitions references impacted by this revision project

<u>Location of reference to be changed</u>	<u>Referenced subclass or group to be changed</u>	<u>Section of definition</u>	<u>Changed to</u>
H01L 27/11585	H01L29/784	Informative references	H01L29/78391